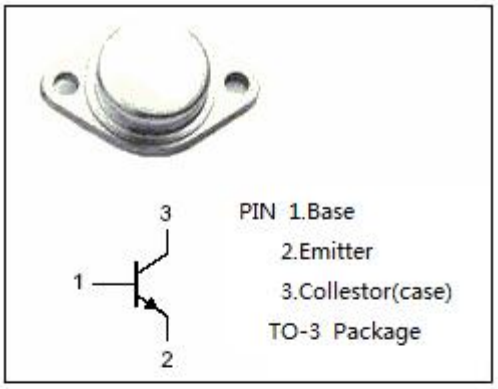
isc Silicon NPN Power Transistor 2N6322

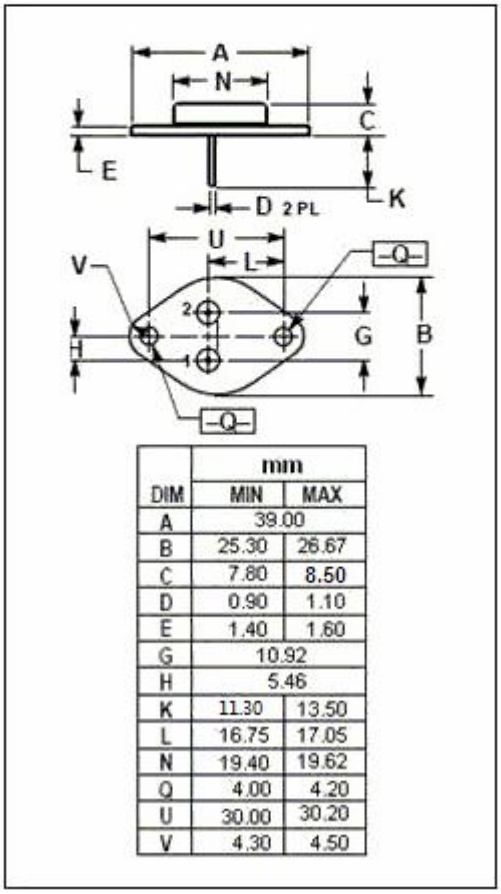
DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 200V(Min)
- High Current Capability
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for power amplifier and high-speed switching applications.





DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	200	V
V_{EBO}	Emitter-Base voltage	5	V
I_C	Collector Current-Continuous	30	A
I_B	Base Current-Continuous	10	A
P_C	Collector Power Dissipation @ T_C=25℃	200	W
T_J	Junction Temperature	200	℃
T_{stg}	Storage Temperature Range	-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	0.5	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 30mA ; I_B= 0	200			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 20A; I_B= 2A			1.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 30A; I_B= 6A			3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 30A ; V_{CE}= 5V			2.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 300V ; I_E= 0			2.0	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 200V ; I_B= 0			1.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			0.5	mA
h_{FE-1}	DC Current Gain	I_C= 5A ; V_{CE}= 5V	40		150	
h_{FE-2}	DC Current Gain	I_C= 20A ; V_{CE}= 5V	12			
h_{FE-3}	DC Current Gain	I_C= 30A ; V_{CE}= 5V	6			
f_T	Current-Gain—Bandwidth Product	I_C=1A ; V_{CE}= 10V	10			MHz